MURD2020CT

Rev.F May.-2016

DATA SHEET

/ Descriptions

TO-252

Ultrafast Recovery Diode in a TO-252 Plastic Package.

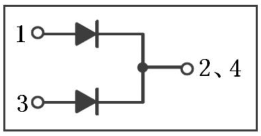
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

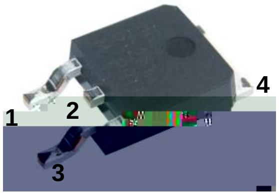
/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode.

/ Equivalent Circuit



/ Pinning



PIN1 Anode PIN 2 4 Cathode PIN 3 Anode

/ h_{FE} Classifications & Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Reverse Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Forward Current	I_F	2 10	A
Non Repetitive Peak Surge Current	I_{FSM}	120	A
Thermal Resistance Junction to Case	R $_{Jc}$	2.8	/W
Operating and Storage Temperature Range	T_j T_{stg}	-55 150	

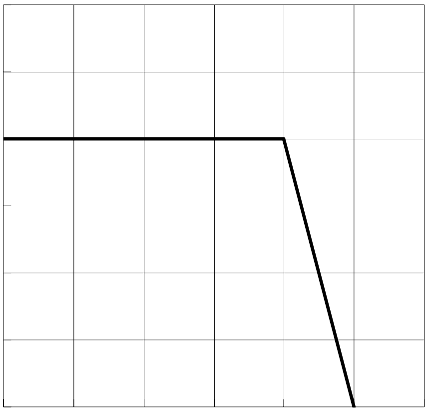
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F=2A Tc=25		0.79		V
		I_F=2A Tc=125		0.65		V
		I_F=10A Tc=25		0.95	1.0	V
		I_F=10A Tc=125		0.84	0.9	V
Instantaneous Reverse Current	I_R Note 1	V_R=200V Ta=25			10	A
		V_R=200V Ta=125			150	A
Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A I_{RR}=0.25A			35	ns

/Notes

1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip

/ Electrical Characteristic Curve



/ Package Dimensions

25	1.75
.60	0.90
0.00	0.10

C	0.45	0.55	L2	1.
D	6.45	6.75	L3	0.
D1	5.10	5.50	K	

TO-252

/ Marking Instructions

BR

MURD2020

CT:

****

Note:

BR:	Company Code
MURD2020	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.